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Form PTO-1 (Rev. 8-83)	O.S. Depart	ment of Commerce	Attorney Docket No. 0)756-2230	Serial No.	
INFOF	RMATION DISCLOSURE STA	TEMENTOO	Applicant: Shunpei Y	'AMAZAKI		
			SFiling Date: September	er 5, 2000	Group:	
	FOR	EIGN PATE	ENT DOCUMENTS	S		
	Document Number	Date	Country	Class	Subclass	Translation Yes No
4/1	1-130131*	06/1989	JP			Abstract
1/1	1-156725*	06/1989	JP			Full
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	Document Number	Date	Country	Class	Subclass	<u>Translati</u> Yes	on No
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6	60-245174*	12/1985	JP		-	Full	+
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	62-147759	07/01/87	JP			Abstract	+
	62-160425*	07/1987	JP			Abstract	+
	63-96636*	04/1988	JP			Abstract	\top
	63-100777*	05/1988	JP			Abstract	\dagger
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	63-237571*	10/1988	JP			Abstract	+
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	1-107237*	04/1989	JP				X
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M	0 161 555*	11/1985	EP	1		1.55	T
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	0 337 457	10/18/89	EP	+		<u> </u>	+
7	49-77537*	07/1974	JP	+		-	X
	53-144297*	12/1978	JP	+		Abstract	+
7	55-011329*	01/1980	JP	+ +		Full	+
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4	57-099729*	06/1982	JP			Abstract	+
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appr priate)
-	5,568,288	10/1996	Yamazaki et al.			
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	5,616,944	04/1997	Mizutani et al.			
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appr priate)
(//	5,289,300*	10/1993	Misawa et al.			
	5,261,156*	11/1993	Mase et al.			
<u>//</u>	5,270,224*	12/1993	Furumura et al.			
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0//	4,860,069*	08/1989	Yamazaki					
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('/	4,885,052*	12/1989	Fan et al.					
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_//	4,891,330*	01/1990	Guha et al.					
/1	4,897,360*	01/1990	Guckel et al.					
	4,905,073*	07/1990	Chem					
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0//	4,949,141*	08/1990	Busta					
4	4,951,113	08/1990	Huang et al.					
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4	4,969,025*	11/1990	Yamamoto					
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4	3-290924* <	12/1991	JP			Abstract	No
	3-246973	11/05/91	JP			Abstract	\dagger
0/	4-245655	09/02/92	JP			Abstract	T
4-	92-18644	10/22/92	Korea				X
+	90-17171	11/15/90	Korea				X
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Atty Docket 075

Serial No. 09/583,087

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Applicants: Shunpei YAMAZAKI

Filing Date: September 05, 2000

Group Art Unit: Unassigned

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-//	60-138909	07/23/1985	JP			Yes No Full Eng
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